

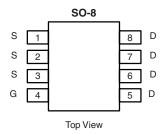
N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
100	0.025 at V _{GS} = 10 V	7.9		
	0.028 at V _{GS} = 6.0 V	7.5		

FEATURES

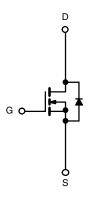
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 175 °C Maximum Junction Temperature
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4486EY-T1-E3 (Lead (Pb)-free)

Si4486EY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter	Symbol	10 s	Steady State	Unit		
Drain-Source Voltage		V _{DS}	100		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 175 °C\3	T _A = 25 °C	- I _D	7.9	5.4		
Continuous Drain Current (T _J = 175 °C) ^a	T _A = 85 °C		6.1	4.2	1	
Pulsed Drain Current		I _{DM}	40		Α	
Avalanche Current	L = 0.1 mH	I _{AR}	30			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)		mH E _{AR}		45		
Continuous Source Current (Diode Conduction) ^a		I _S	3.1	1.5	Α	
M	T _A = 25 °C	P _D	3.8	1.8	W	
Maximum Power Dissipation ^a	T _A = 85 °C		2.3	1.1	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariana baratian ta Andrianta	t ≤ 10 s	R _{thJA}	33	40	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		70	85		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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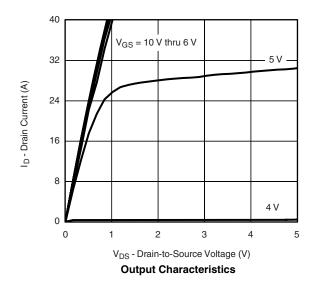
Parameter	Symbol Test Conditions		Min.	Тур.	Max.	Unit	
Static			<u>'</u>	<u>'</u>	<u> </u>		
Gate Threshold Voltage V _{GS(th}		$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V V _{DS} = 80 V, V _{GS} = 0 V, T _J = 85 °C			1	μΑ	
					20		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Drain-Source On-State Resistance ^a	В	$V_{GS} = 10 \text{ V}, I_D = 7.9 \text{ A}$	0.021		0.025	Ω	
	R _{DS(on)}	V _{GS} = 6.0 V, I _D = 7.5 A		0.023	0.028		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 7.9 \text{ A}$		35		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 3.1 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b	•						
Total Gate Charge	Q_g			36	44	nC	
Gate-Source Charge	Q _{gs}	Q_{gs} $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.9 \text{ A}$		10			
Gate-Drain Charge	Q_{gd}			8.6			
Gate Resistance	R_{g}		0.5	1.27	2.2	Ω	
Turn-On Delay Time	t _{d(on)}			20	40		
Rise Time	t _r	V_{DD} = 50 V, R_L = 50 Ω		10	20		
Turn-Off Delay Time	$t_{d(off)}$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 6 \Omega$		46	90	ns		
Fall Time	t _f			26	50		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3.1 A, dI/dt = 100 A/μs		50	80		

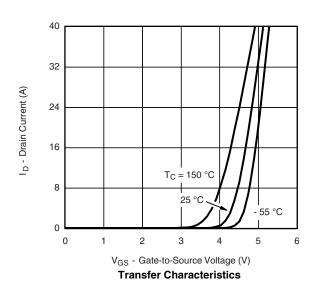
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

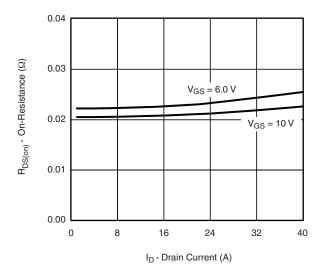




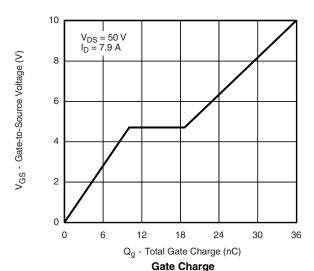


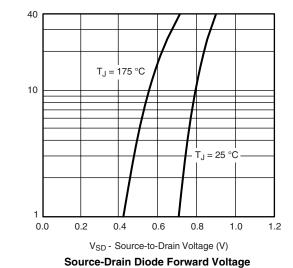


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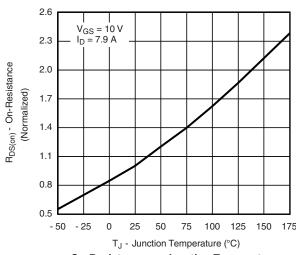


On-Resistance vs. Drain Current

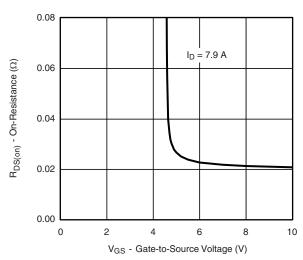




3500 3000 C_{iss} 2500 C - Capacitance (pF) 2000 1500 1000 C_{rss} 500 Coss 0 0 10 30 50 60



On-Resistance vs. Junction Temperature

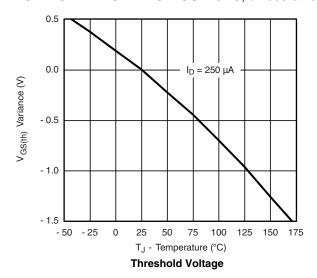


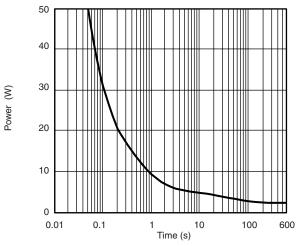
Is - Source Current (A)

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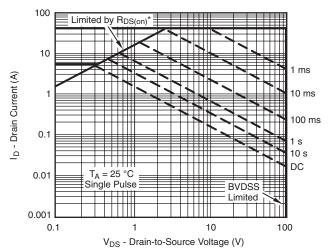
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



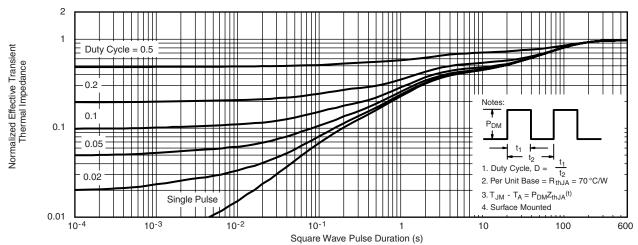


Single Pulse Power



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

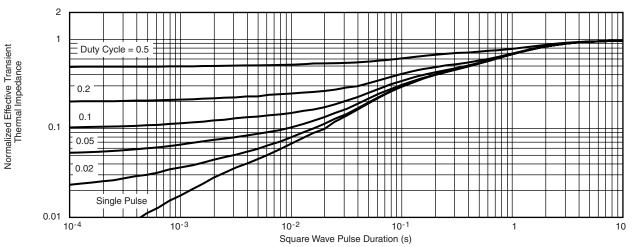
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg271234.



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